



# 2CL122,2CL123,2CL125,2CL126,2CL127

## GLASS PASSIVATED SILICON ULTRAHIGH VOLTAGE,

## ULTRAFAST RECOVERY DIODE

### Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611



### TECHNICAL DATA:

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications					Test Condition
			2CL122	2CL123	2CL125	2CL126	2CL127	
Use for	Ultra-high-frequency, high-voltage boost, rectifier circuit.							
Store temperature	T	°C	-55~+130					
Quality Class			JP, JT, GS, G					
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	KV	10	10	1.5	4.5	8	
Average Forward Current	I <sub>F(AV)</sub>	A	0.2	0.2	1.0	0.4	0.4	
Average Forward Voltage	V <sub>F</sub>	V	20	15	3	8	15	I=I <sub>F(AV)</sub>
Non-repeat Forward Surge Current	I <sub>FSM</sub>	A	4	10	20	8	8	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I <sub>RM1</sub>	uA	5	5	5	5	10	V <sub>R</sub> =V <sub>RRM</sub> , Ta=25°C
Peak Reverse Current	I <sub>RM2</sub>	uA	20	30	50	50	50	V <sub>R</sub> =V <sub>RRM</sub> , Ta=125°C (105°C for 2CL122)
Junction Temperature	T <sub>jm</sub>	°C	125	125	125	125	125	
Reverse Recovery Time	t <sub>rr</sub>	uS	0.1	0.06	0.1	0.1	0.1	V <sub>R</sub> =10V,I <sub>F</sub> =50mA,R <sub>L</sub> =75ohm

### Outline and Dimensions: